NPN Silicon Epitaxial Planar Transistor

for switching and AF amplifier applications.

The transistor is subdivided into six groups, D, E, F, G, H and I, according to its DC current gain.

On special request, these transistors can be manufactured in different pin configurations.



1. Emitter 2. Base 3. Collector

TO-92 Plastic Package Weight approx. 0.19g

Absolute Maximum Ratings ($T_a = 25^{\circ}C$)

	Symbol	Value	Unit
Collector Base Voltage	V _{CBO} 50		V
Collector Emitter Voltage	V _{CEO}	30	V
Emitter Base Voltage	V _{EBO}	5	V
Collector Current	I _C	30	mA
Power Dissipation	P _{tot}	400	mW
Junction Temperature	Tj	150	°C
Storage Temperature Range	Ts	-55 to +150	°C









Characteristics at $T_{amb}=25$ °C

	Symbol	Min.	Тур.	Max.	Unit
DC Current Gain					
at V_{CE} =5V, I _C =1mA					
Current Gain Group D	h _{FE}	28	-	45	-
E	h _{FE}	39	-	60	-
F	h_{FE}	54	-	80	-
G	h _{FE}	72	-	108	-
н	h_{FE}	97	-	146	-
I	h _{FE}	132	-	198	-
Collector Base Breakdown Voltage					
at I _C =100μA	V _{(BR)CBO}	50	-	-	V
Collector Emitter Breakdown Voltage					
at I _C =1mA	$V_{(BR)CEO}$	30	-	-	V
Emitter Base Breakdown Voltage					
at I _E =100μA	$V_{(BR)EBO}$	5	-	-	V
Collector Cutoff Current					
at V_{CB} =50V	I _{CBO}	-	-	100	nA
Emitter Cutoff Current					
at V_{CB} =5V	I _{EBO}	-	-	100	nA
Collector Emitter Saturation Voltage					
at I _C =10mA, I _B =1mA	V _{CE(sat)}	-	0.08	0.3	V
Base Emitter Voltage					
at V_{CE} =5V, I _C =1mA	$V_{\text{BE(on)}}$	0.60	0.7	0.75	V
Collector Base Capacitance					
at V_{CB} =10V, f=1MHz	C _{CBO}	-	1.5	-	pF
Gain Bandwidth Product					
at V_{CE} =5V, I _C =1mA	f⊤	150	370	-	MHz







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